

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D $T_A = 25^\circ\text{C}$
-20V	70m Ω @ $V_{GS} = -4.5\text{V}$	3.5 A
	90m Ω @ $V_{GS} = -2.5\text{V}$	3.0 A

Description and Applications

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Battery Management
- Load Switch
- Battery Protection

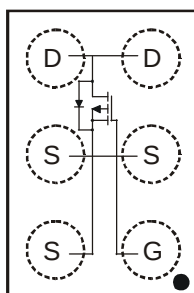
Features and Benefits

- Low Q_g & Q_{gd}
- Small Footprint
- Low Profile 0.62mm height
- Lead Free By Design/RoHS Compliant (Note 1)**
- "Green" Device Halogen and Antimony Free (Note 2)**
- Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: U-WLB1510-6
- Terminal Connections: See Diagram Below
- Weight: 0.0018 grams (approximate)

U-WLB1510-6



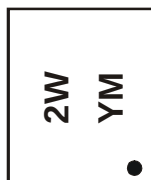
Top View

Ordering Information (Note 3)

Part Number	Case	Packaging
DMP2070UCB6-7	U-WLB1510-6	3000/Tape & Reel

- Notes:
- No purposefully added lead.
 - Diodes Inc.'s "Green" policy can be found on our website at <http://www.diodes.com>.
 - For packaging details, go to our website at <http://www.diodes.com>

Marking Information



2W = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: Y = 2011)
 M = Month (ex: 9 = September)

Date Code Key

Year	2011	2012	2013	2014	2015	2016	2017
Code	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	-20	V
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current (Note 4) V _{GS} = -4.5V	Steady State	T _A = 25°C	I _D	-2.5	A
		T _A = 70°C		-2.0	
Continuous Drain Current (Note 5) V _{GS} = -4.5V	Steady State	T _A = 25°C	I _D	-3.5	A
		T _A = 70°C		-2.8	
Pulsed Drain Current (Note 6)			I _{DM}	-12	A
Maximum Continuous Body Diode Forward Current (Note 5)			I _S	-1.8	A

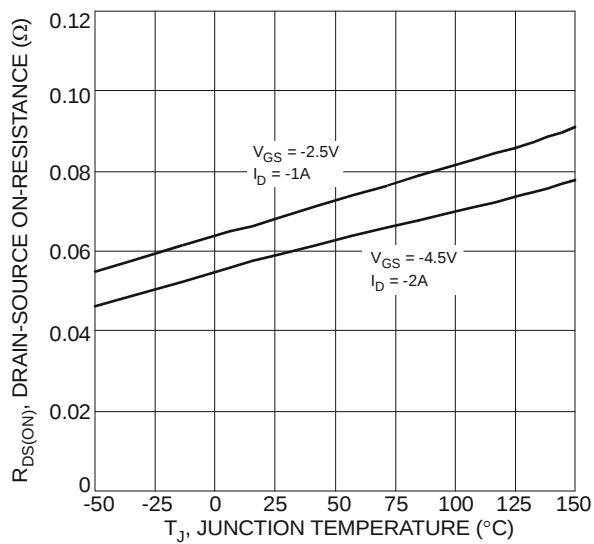
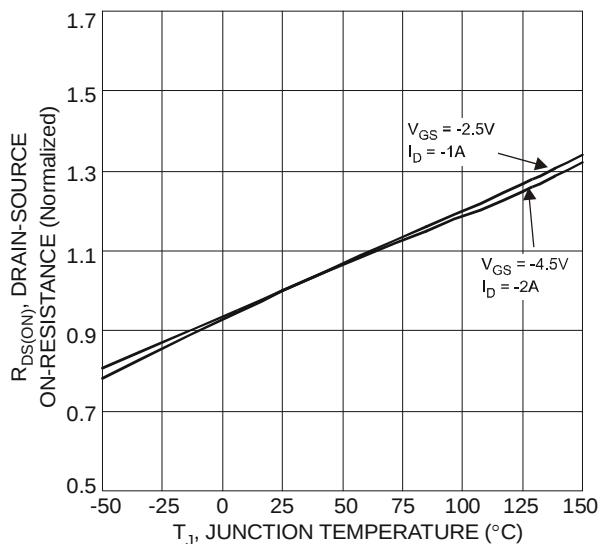
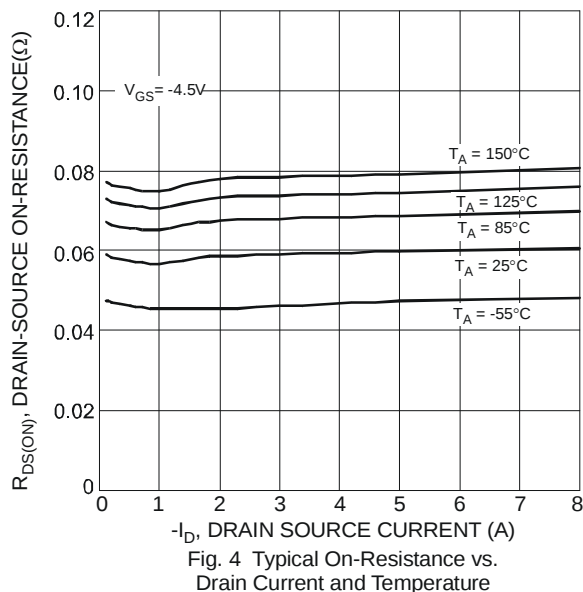
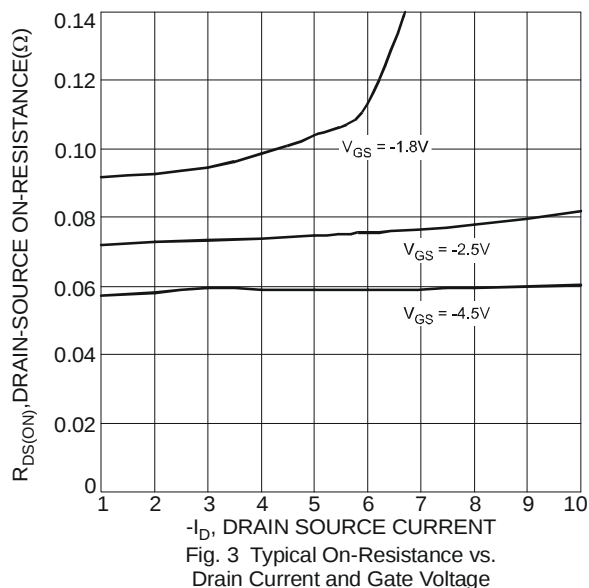
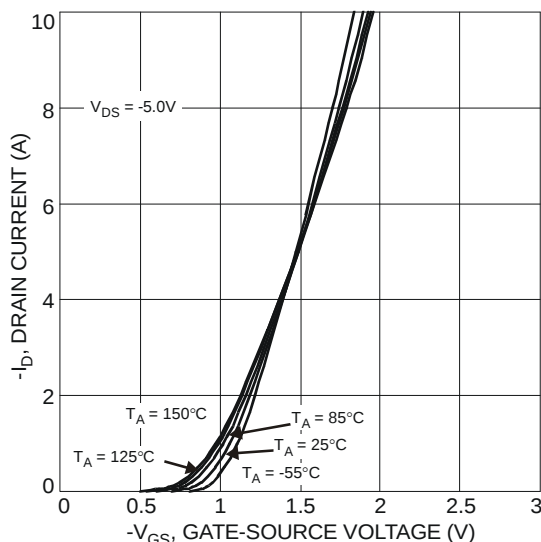
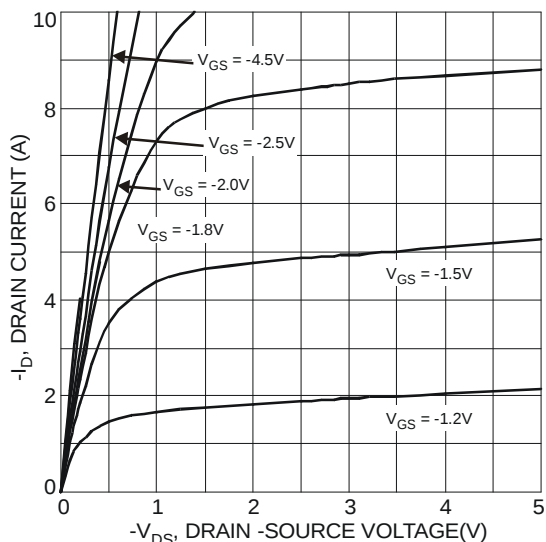
Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 4)	P _D	0.92	W
Total Power Dissipation (Note 5)	P _D	1.47	W
Thermal Resistance, Junction to Ambient (Note 4)	R _{θJA}	136	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	84	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	-	-	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current @T _C = 25°C	I _{DSS}	-	-	-1	μA	V _{DS} = -16V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	-0.4	-0.6	-1.0	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(on)}	-	55	70	mΩ	V _{GS} = -4.5V, I _D = -1A
			70	90		V _{GS} = -2.5V, I _D = -1A
			90	110		V _{GS} = -1.8V, I _D = -1A
			110	150		V _{GS} = -1.5V, I _D = -1A
Forward Transfer Admittance	Y _{fs}	-	12	-	S	V _{DS} = -10V, I _D = -1A
Diode Forward Voltage (Note 5)	V _{SD}	-	-0.7	-1	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	-	210	-	pF	V _{DS} = -10V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	-	92	-	pF	
Reverse Transfer Capacitance	C _{rss}	-	38	-	pF	
Series Gate Resistance	R _G	-	5.3	-	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (4.5V)	Q _g	-	2.9	-	nC	V _{GS} = -4.5V, V _{DS} = -10V, I _D = -1A
Gate-Source Charge	Q _{gs}	-	0.3	-	nC	
Gate-Drain Charge	Q _{gd}	-	0.5	-	nC	
Turn-On Delay Time	t _{D(on)}	-	7.3	-	ns	V _{DD} = -10V, V _{GS} = -4.5V, I _{DS} = -1A, R _G = 20Ω
Turn-On Rise Time	t _r	-	14.0	-	ns	
Turn-Off Delay Time	t _{D(off)}	-	42.6	-	ns	
Turn-Off Fall Time	t _f	-	32	-	ns	

- Notes:
- Device mounted on FR-4 PCB with minimum recommended pad layout.
 - Device mounted on FR4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu
 - 300ms pulse, pulse duty cycle ≤ 2%
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.



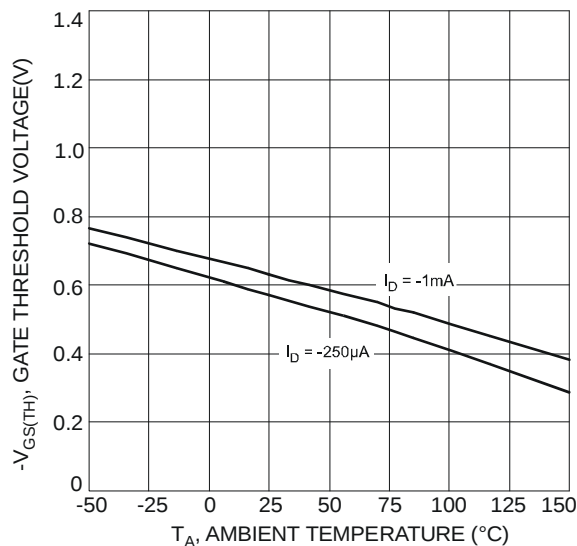


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

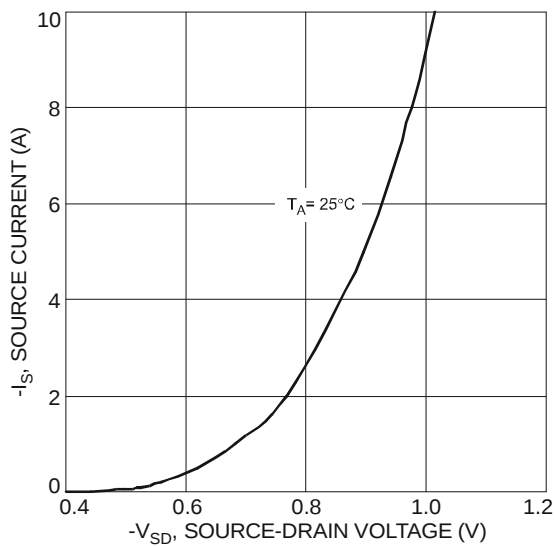


Fig. 8 Diode Forward Voltage vs. Current

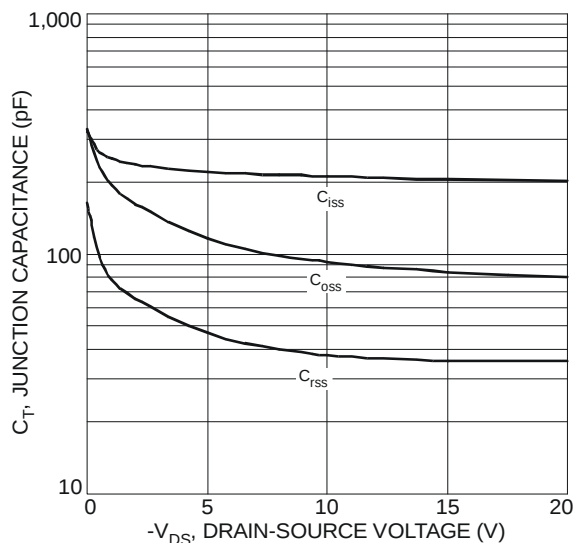


Fig. 9 Typical Junction Capacitance

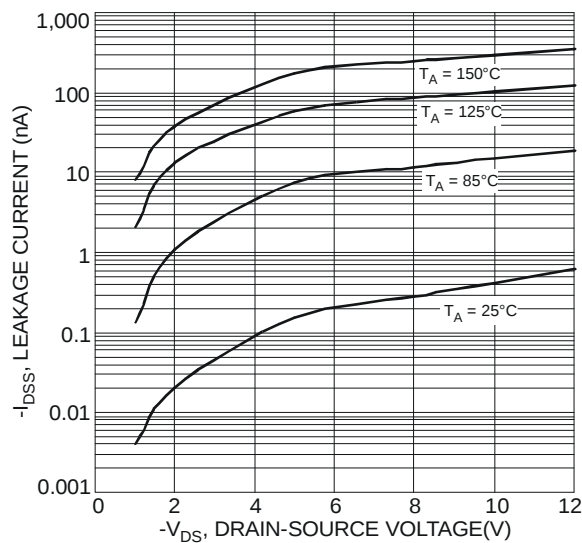


Fig. 10 Typical Drain-Source Leakage Current vs. Voltage

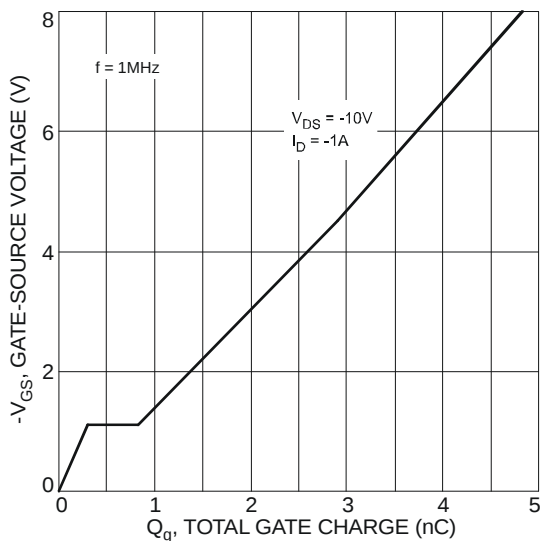


Fig. 11 Gate-Charge Characteristics

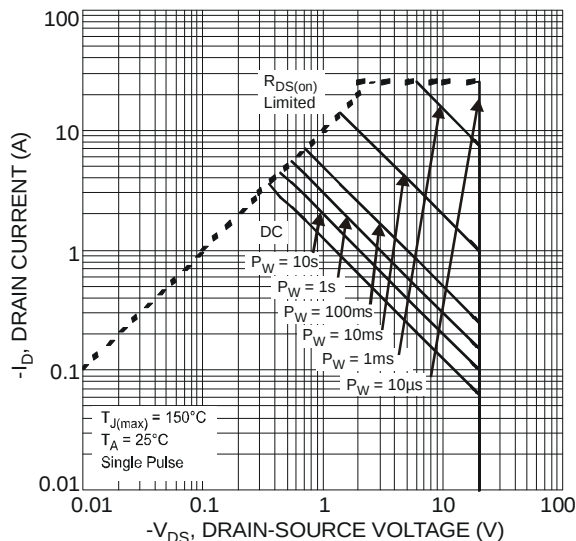
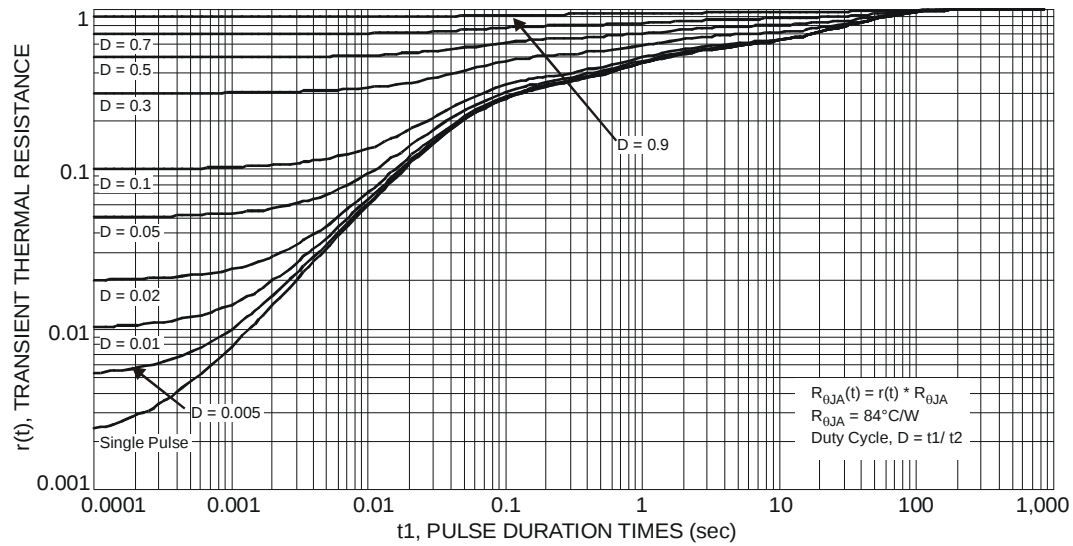
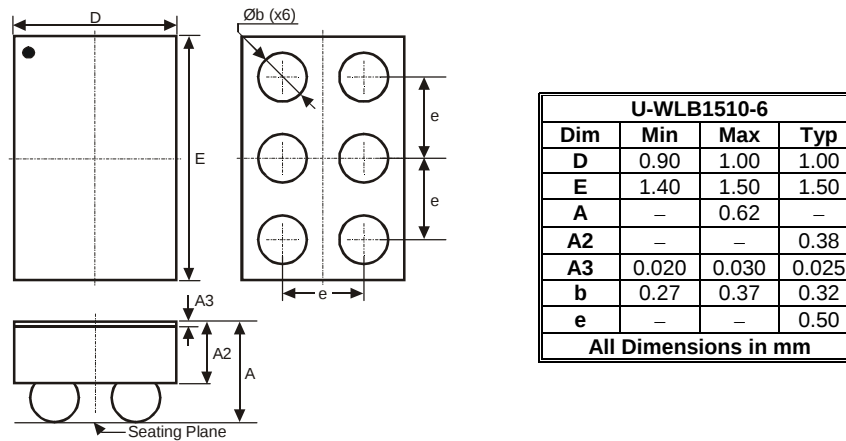


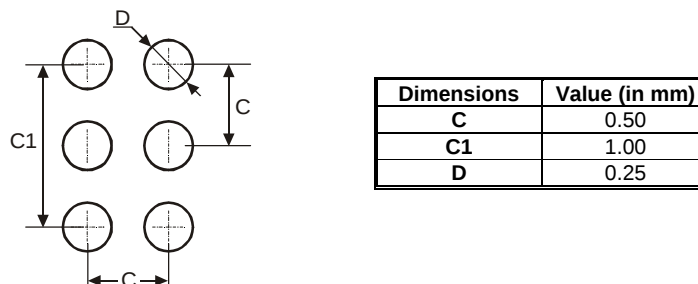
Fig. 12 SOA, Safe Operation Area



Package Outline Dimensions



Suggested Pad Layout



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